insulator transist transist on-insula on-insul		ب ا	Туре	L #	Hits	ch Text	DBs	Time Stamp	Comments
BRS L2 35266 silicon-on-insulator thin JPO; 200 tfft 1 and (1dd low\$2 adj U\$PAT; 200 impurity mdd) and spacer\$2 UBPAT; 200 ((silicide) near31 ((source and drain)adj (electrod\$2 wir\$4))) and 3 us-PGP 12: and drain) and ((source and drain)) and (source and drain)) and (source and drain) and and and and and spacer\$2 DERWEN 12: drain and drain) and (source and drain) and spacer\$2 DERWEN 12: drain and drain) and spacer\$2 DERWEN 12: drain and drain and spacer\$2 DERW	Ь	B 72	ώ 	L1	502	silicon-on-insulator icon adj insulator thin film adj transistor\$2	PAT; -PGP	2002/11	
BRS L3 1040 impurity mdd) and spacer\$2 US-PGP 12: ((silicide) near31 US-PGP 12: ((source and drain) adj (electrod\$2 wir\$4))) and 3 BRS L5 3 and drain) adj (electrod\$2 US-PGP 12: ((silicide) same((source US-PGP) 12: ((silicide) near31 (source US-PGP) 12: ((silicide) near31 (source US-PGP) 12: and drain) adj (electrod\$2 US-PGP) 12: ((silicide) same (source and US-PGP) 12: ((silicide) same (source US-PGP) 12: ((silicide) same (source and US-PGP) 12: ((silicide) same (source and US-PGP) 12: ((silicide) same (source and US-PGP) 12: ((silicide) same (source US-PGP) 12: (silicide) same (source US-PGP)	2	BR	Š	L2	526	silicon-on-insulator icon adj insulator thin film adj transistor\$2	EPO; JPO; DERWEN	2002/11,	
BRS L4 0 ((silicide) near31 USPAT; 200 ((source and drain)adj US-PGP 12: ((silicide) same((source USPAT; 200 and drain)adj (electrod\$2 wir\$4))) and 3 UB 12: ((silicide) same((source USPAT; 200 and drain)adj (electrod\$2 UB 12: ((silicide) near31 (source USPAT; 200 and drain)) and (source and US-PGP 12: ((silicide) same (source and US-PGP 12: ((silicide) and ((source and US-PGP 12: ((silicide) and (source and US-PGP 12: ((silicide) and (source USPAT; 200 and drain) adj (electrod\$2 UB 12: ((silicide) and (source USPAT; 200 and drain) adj (electrod\$2 DERWEN 12: ((silicide) and (source USPAT; 200 and drain) adj (electrod\$2 DERWEN 12: ((silicide) and (source USPAT; 200 and drain) adj (electrod\$2 DERWEN 12: ((silicide) and (source USPAT; 200 and drain) adj (electrod\$2 DERWEN 12: ((silicide) and (source USPAT; 200 and drain) adj (electrod\$2 DERWEN 12:	ω	B R	ίς	Г3	1040	(ldd low\$2 adj mdd)and spacer\$2	PAT;	2002/11/28 12:58	
BRS L5 3 and drain) adj (electrod\$2 US-PGF 12: ((silicide) same((source USPAT; 200 wir\$4))) and 3 ((silicide) near31 (source U\$PAT; 200 and drain)) and ((source and drai	4	BR	S	L4	0	(silicide) near31 source and drain)adj lectrod\$2 wir\$4)))and 3	PAT;	2002/11/28 12:52	
BRS L6 0 ((silicide) near31 (source USPAT; 2002/11, and drain)) and ((source and Wir\$4)) and 3 (source and Wir\$4)) and spacer\$2 DERWEN 12:47 (silicide) and ((source and Wir\$4))) and 8 (source DERWEN 12:48) (silicide) and spacer\$2 DERWEN 12:48 (silicide) and	σ	BR	ŝ	L5	ω	(silicide) same((source d drain)adj (electrod\$2 r\$4)))and 3	PAT; -PGP	2002/11/28	
BRS L7 17 and drain) and (source drain) and (source and wir\$4) and 3 BRS L8 20 2 and (ldd low\$2 adj JPO; 2002/11, impurity mdd) and spacer\$2 DERWEN 12:48 BRS L9 0 and drain) adj (electrod\$2 DERWEN 12:48 Compute the same (source and US-PGP 12:47) EPO; 2002/11, impurity mdd) and spacer\$2 DERWEN 12:48 Compute the same (source and US-PGP 12:47) EPO; 2002/11, impurity mdd) and spacer\$2 DERWEN 12:48 Compute the same (source and US-PGP 12:47) EPO; 2002/11, impurity mdd) and (source and US-PGP 12:48) Compute the same (source and US-PGP 12:47) EPO; 2002/11, impurity mdd) and (source and US-PGP 12:48) Compute the same (source and US-PGP 12:47) EPO; 2002/11, impurity mdd) and spacer\$2 DERWEN 12:52	D	88	ω	L 6	0	silicide) near31 (source drain))and((source and in)adj (electrod\$2 \$4))and 3	10 10	/11,	
BRS L8 20 2 and (ldd low\$2 adj JPO; 2002/11, impurity mdd) and spacer\$2 DERWEN 12:48 ((silicide) and ((source JPO; 2002/11, and drain) adj (electrod\$2 DERWEN 12:52	7	ਸ਼ੁਲ	ŝ	L7	17	silicide) same (source drain))and((source and in)adj (electrod\$2 \$4))and 3	USPAT; US-PGP UB	2002/11/28 12:47	٠
BRS L9 0 ((silicide) and ((source JPO; 2002/11, wir\$4)))and 8	ω	BF	ŝ	L8	20	(1dd low\$2 adj mdd)and spacer\$2	EPO; JPO; DERWEN T	2002/11/28 12:48	
	٥	BF	ŝ	Т9	0	(silicide) and ((source d drain)adj (electrod\$2 r\$4)))and 8	EPO; JPO; DERWEN	2002/11/28 12:52	